

SIDC110D170H

Fast switching diode chip in EMCON 3-Technology

FEATURES:

- 1700V EMCON 3 technology 200 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

EUPEC power modules



Applications:

• resonant applications, drives

| Chip Type | V_R | I _F | Die Size | Package | Ordering Code |
|--------------|-------|----------------|-----------------------------|--------------|-----------------------|
| SIDC110D170H | 1700V | 200A | 10.5 x 10.5 mm ² | sawn on foil | Q67050-A4179- A001 |

MECHANICAL PARAMETER:

| WECHANICAL PARAWETER: | T | | | | |
|---------------------------------|---|-----------------|--|--|--|
| Raster size | 10.5 x 10.5 | | | | |
| Area total / active | 110.25 / 90.9 | mm ² | | | |
| Anode pad size | 8.48 x 8.48 | | | | |
| Thickness | 200 | | | | |
| Wafer size | 150 | mm | | | |
| Flat position | 180 | deg | | | |
| Max. possible chips per wafer | 122 pcs | | | | |
| Passivation frontside | Photoimide | | | | |
| Anode metallization | 3200 nm Al Si Cu | | | | |
| Cathode metallization | Ni Ag –system suitable for epoxy and soft solder die bonding | | | | |
| Die bond | electrically conductive glue or solder | | | | |
| Wire bond | AI, ≤500μm | | | | |
| Reject Ink Dot Size | Ø 0.65mm; max 1.2mm | | | | |
| Recommended Storage Environment | store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C | | | | |



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Maximum Ratings

| Parameter | Symbol | Condition | Value | Unit |
|---|----------------------------|----------------------------------|---------|------|
| Repetitive peak reverse voltage | V_{RRM} | | 1700 | V |
| Continuous forward current limited by T_{jmax} | I _F | | 200 | |
| Single pulse forward current (depending on wire bond configuration) | I _{FSM} | $t_P = 10 \text{ ms sinusoidal}$ | 930 | А |
| Maximum repetitive forward current limited by T_{jmax} | I _{FRM} | | 400 | |
| Operating junction and storage temperature | $T_{\rm j}$, $T_{ m stg}$ | | -55+150 | °C |

$\textbf{Static Electrical Characteristics} \text{ (tested on chip), } \textit{T}_{j}\text{=25 °C, unless otherwise specified}$

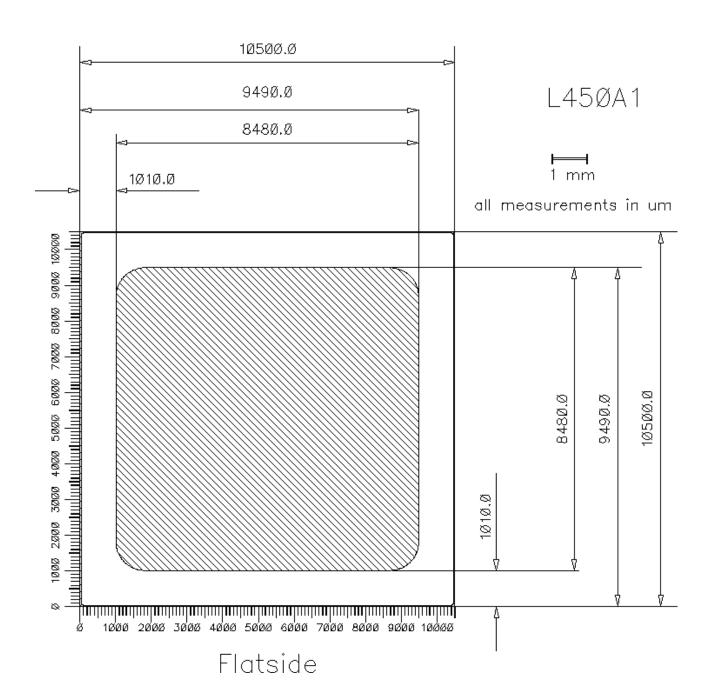
| Parameter | Symbol | Condi | Value | | | Unit | |
|---------------------------------|-----------------|------------------------|-----------------------------|------|------|------|----|
| i arameter | Symbol | Conditions | | min. | Тур. | max. | |
| Reverse leakage current | I_{R} | V _R =1700V | <i>T_j</i> =25 °C | | | 27 | μΑ |
| Cathode-Anode breakdown Voltage | V _{Br} | I _R =0.25mA | <i>T_j</i> =25°C | 1700 | | | V |
| Forward voltage drop | V _F | I _F =200A | <i>T_j</i> =25 °C | | 1.8 | | V |

Dynamic Electrical Characteristics, at $T_i = 25$ °C, unless otherwise specified, tested at component

| Parameter | Symbol | Conditions | | Value | | | Unit |
|-------------------------|--------------------|--|-----------------------------|-------|------|------|------|
| rarameter | Symbol | | | min. | Тур. | max. | 7 |
| Peak recovery current | I_{RRM1} | I _F =200A | $T_j = 25 ^{\circ}C$ | | 171 | | Α |
| | I_{RRM2} | $di/dt=960 A/ms$ $V_R=900 V$ | $T_j = 125 ^{\circ}C$ | | 204 | | |
| Reverse recovery charge | Q _{rr1} | I _F =200A di/dt=960A/ m s | <i>T_j</i> =25 °C | | 47.5 | | μC |
| | Q _{rr2} | $V_R=900V$ | T _j =125°C | | 82.5 | | |
| Peak recovery energy | E _{rec 1} | I _F =200A | $T_{\rm j}$ = 25 ° C | | 32.5 | | |
| | E _{rec2} | di/dt=960A/ m s V _R =900V | T _j =125°C | | 57.5 | | mJ |



CHIP DRAWING:





SIDC110D170H

FURTHER ELECTRICAL CHARACTERISTICS:

| This chip data sheet refers to the | INFINEON TECHNOLOGIES / | tbd |
|------------------------------------|-------------------------|-----|
| device data sheet | EUPEC | tou |

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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